

APR 08 2005

US DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEINFORMATION DISCLOSURE
STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 1 of 2 Attorney Docket No. 800_134

Complete if Known

Application Number	10/813,565
Filing Date	March 30, 2004
First Named Inventor	Yuji HORI
Art Unit	2811
Examiner Name	Cuong Quang Nguyen
Confirmation No.	4125

U.S. PATENT DOCUMENTS

Exam. Initial		Document Number	Date	Name	Our Docket No.	Class	Sub Class	Filing Date
Ch	AA	2002/0053679 A1	05/09/2002	Nikolaev et al.				
Ch	AB	2002/0136932 A1	09/26/2002	Yoshida				
Ch	AC	5,488,233	01/30/1996	Ishikawa et al.				
Ch	AD	5,740,192	04/14/1998	Hatano et al.				

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Sub Class	Translation	Abstract
Ch	AE	1 211 737 A2	06/05/2002	EP				
Ch	AF	00/63961	10/26/2000	WO				

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages etc.)

Ch	AG	SHIBATA T ET AL: "Characterization of high-quality epitaxial AlN films grown by MOVPE", GAN AND RELATED ALLOYS - 2001. Symposium (Materials Research Society Symposium Proceedings Vol. 693), GAN AND RELATED ALLOYS - 2001, BOSTON, MA, USA, 26-30 JAN. 2001, pages 541-544, XP001168620, 2002, Warrendale, PA, USA, Mater. Res. Soc., USA *abstract*
Ch	AH	SAXLER A ET AL: "High quality aluminum nitride epitaxial layers grown on sapphire substrates", APPLIED PHYSICS LETTERS, 17 JAN. 1994, USA, vol. 64, no. 3, pages 339-341, XP002256572, ISSN: 0003-6951 *page 340*
Ch	AI	OHBA Y ET AL: "Growth of high-quality AlN and AlN/GaN/AlN heterostructure on sapphire substrate" JAPANESE JOURNAL OF APPLIED PHYSICS, PART 2 (LETTERS), 15 AUG. 1996, PUBLICATION OFFICE JAPANESE JOURNAL APPL. PHYS. JAPAN, vol. 35, no. 8B, pages L1013-L1015, XP002256573, ISSN: 0021-4922 *L1013-L1014*
Ch	AJ	KAUFMANN U ET AL: "Hole conductivity and compensation in epitaxial GaN:Mg layers" PHYSICAL REVIEW B (CONDENSED MATTER), 15 OCT. 2000, APS THROUGH AIP, USA, vol. 62, no. 16, pages 10867-10872, XP002256574, ISSN: 0163-1829 *page 10867*
Ch	AK	SANTIC B ET AL: "Current transport mechanism and I-V characteristics of titanium and indium contacts to p-type GaN" MATERIALS SCIENCE & ENGINEERING B (SOLID-STATE MATERIALS FOR ADVANCED TECHNOLOGY), 30 MAY 2002, ELSEVIER, SWITZERLAND, vol. B93, pages 202-206, XP002255818, ISSN: 0921-5107, *the whole document*

INFORMATION DISCLOSURE
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Sheet	2	of	2	Attorney Docket No.	800_134

<i>AK</i>	<i>AK</i>	BHARGAVA R N: "The role of impurity in doped nanocrystals" 1996 INTERNATIONAL CONFERENCE ON LUMINESCENCE AND OPTICAL SPECTROSCOPY OF CONDENSED MATTER, PRAGUE, CZECH REPUBLIC, 18-23 AUG. 1996, vol. 72-74, pages 46-48, XP002255817, Journal of Luminscence, June 1997, Elsevier, Netherlands, ISSN: 0022-2313 *the whole document*
<i>AL</i>	<i>AL</i>	ZHANG J ET AL: "INGAN SELF-ASSEMBLED QUANTUM DOTS GROWN BY METALORGANIC CHEMICAL-VAPOR DEPOSITION WITH INDIUM AS THE ANTISURFACTANT" APPLIED PHYSICS LETTERS, AMERICAN INSTITUTE OF PHYSICS, NEW YORK, US, vol. 80, no. 3, 21 January 2002 (2002-01-21), pages 485-487, XP001093504, ISSN: 0003-6951 *page 485*

Examiner:	<i>QGS</i>	Date Considered:	<i>05-01-05</i>
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

*In accordance with the Notice dated July 11, 2003 on the PTO website, we are not enclosing copies of any of the above U.S. references.